SB170 - SB1100



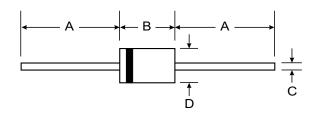
1.0A HIGH VOLTAGE SCHOTTKY BARRIER RECTIFIER

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- Surge Overload Rating to 25A Peak
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Application
- High Temperature Soldering: 260°C/10 Second at Terminal
- Plastic Material: UL Flammability Classification Rating 94V-0

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads -Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.3 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-41					
Dim	Min	Max			
Α	25.4	—			
В	4.1	5.2			
С	0.71	0.86			
D	2.0	2.7			
All Dimensions in mm					

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic		SB170	SB180	SB190	SB1100	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	70	80	90	100	v
RMS Reverse Voltage	V _{R(RMS)}	49	56	63	70	V
Average Rectified Output Current @ T _T = 85°C	l _o	1.0				Α
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)		25				А
Forward Voltage @ $I_F = 1.0A$ @ $T_A = 25^{\circ}C$		0.80				V
Peak Reverse Current@ $T_A = 25^{\circ}C$ at Rated DC Blocking Voltage@ $T_A = 100^{\circ}C$		0.5 10				mA
Typical Junction Capacitance (Note 2)		80				pF
Typical Thermal Resistance Junction to Lead		15				K/W
Typical Thermal Resistance Junction to Ambient (Note 1)		50				K/W
Operating and Storage Temperature Range		-65 to +125				°C

Notes: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

